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TRANSMITTAL			Application	Serial Number	10/696	10/696,994	
			Filing Date		October 30, 2003		
			First Named	Inventor	Currie		
			Group Art U	Init	2811	2811	
			Examiner N	ame	Not ye	Not yet assigned	
			Attorney Do	cket No.	ASC-063		
			Patent No.		Not ap	Not applicable	
			Issue Date		Not applicable		
		ENC	CLOSURES (c.	heck all that apply)	<u> </u>		
☐ F	ee Transmittal Form		Copy of Notice	e to File Missing		Notice of Appeal to Board	
	☐ Check Attached ☐ Copy of Fee Transmittal Form		Parts of Applic			of Patent Appeals and Interferences Appeal Brief (in triplicate)	
	Amendment/Response		Request For Co Examination (I Transmittal			Status Inquiry	
	☐ After Final				\boxtimes	Return Receipt Postcard	
	☐ Affidavits/declaration(s) ☐ Letter to Official ☐ Draftsperson including Drawings		Power of Attorney (Revocation of Prior Powers)		\boxtimes	Certificate of First Class Mailing under 37 C.F.R. 1.8	
	[Total Sheets]		Terminal Discl	aimer		Certificate of Facsimile Transmission under 37 C.F.R. 1.8	
	Petition for Extension of Time			aration and Power Utility or Design		Additional Enclosure(s) (please identify below)	
\boxtimes	Information Disclosure Statement		Small Entity S	tatement			
	Form PTO-1449 Copies of IDS Citations B1-B2 and C1-C7		CD(s) for large table or computer program				
	Certified Copy of Priority Document(s)			fter Allowance			
			Request for Certificate of Correction Certificate of Correction (in duplicate)				
CORR	RESPONDENCE ADDRESS		SIGNATURE BLO	ОСК	Dogmontfully orber two d		
Direct all correspondence to: Patent Administrator Testa, Hurwitz & Thib High Street Tower 125 High Street Boston, MA 02110 Tel. No.: (617) 248-70 Fax No.: (617) 248-71			ibeault, LLP	Respectfully submitted, Date: January, 2005 Tel. No.: (617) 248-7453 ax No.: (617) 790-0361 Attorney for Applicants Testa, Hurwitz & Thibeault, LLP High Street High Street Boston, MA 02110			





IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S):

Currie et al.

CONFIRMATION NO.:

7878

SERIAL NO.:

10/696,994

GROUP NO.:

2811

FILING DATE:

October 30, 2003

EXAMINER:

Not yet assigned

TITLE:

Methods for Preserving Strained Semiconductor Substrate Layers

During CMOS Processing

CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 140 day of January, 2005.

Lisa Marie Solis

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Submitted herewith is/are:

- 1. Transmittal Form (1 page);
- 2. Information Disclosure Statement (2 pages);
- 3. Form PTO-1449 (1 page);
- 4. Copy of cited references B1-B2 and C1-C7; and
- 5. Return receipt postcard.



PATENT Attorney Docket No. ASC-063 (366/41)

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Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of foreign patents and non-patent publications are enclosed.

Applicants wish to inform the Examiner about the following related patent applications, and the contents of their file wrappers, including all Office Actions issued therein:

U.S.S.N. 09/665,139 filed on September 19, 2000.

U.S.S.N. 10/392,338 filed on March 19, 2003, and published on December 18, 2003, as U.S. Application No. 2003/0230233 (Ref. A7).

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1)	within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the merits, or before the mailing of a first Office action after the filing of a request for continued examination under 37 C.F.R. 1.114; or
(2)	after the period defined in (1) but before the mailing date of a final action or a notice

of allowance under 37 C.F.R. 1.311, and

Information Disclosure Statement Serial No. 10/696,994 Page 2 of 2

		•	ee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or
	(3)	after the maili of the issue fe	ng date of a final action or notice of allowance but before the payment e, AND
			statement is below, AND etition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included herein.
It is re	espectfi	ılly requested t	hat each of the patents and publications listed on the attached Form
PTO-1449,	and oth	ner information	a contained herein, be made of record in this application.
			STATEMENT
As rec	quired ı	ınder 37 C.F.R	. 1.97(e), Applicant(s), through the undersigned, hereby state either that
[check the	approj	oriate space o	nly if either (2) or (3) is checked on the previous page and the
Statement	is requ	ired]:	
	1.	first cited foreign a	m of information contained in the Information Disclosure Statement was d in any communication from a foreign patent office in a counterpart application not more than three months prior to the filing of the ion Disclosure Statement; or
	2.	cited in a applicati making r Disclosu 1.56(c) r	of information contained in the Information Disclosure Statement was a communication from a foreign patent office in a counterpart foreign on, and, to the knowledge of the person signing this Statement after reasonable inquiry, no item of information contained in the Information are Statement was known to any individual designated in 37 C.F.R. more than three months prior to the filing of the Information are Statement.
			Respectfully submitted,
Date: Janu Reg. No. 50		, 2005	Mark L. Beloborodov Attorney for Applicants Testa, Hurwitz, & Thibeault, LLP
Tel. No.: (6	•		High Street Tower
Fax No.: (6	17) 248	s-7100	125 High Street Boston, Massachusetts 02110
3162042-1			

Sheet 1 of 1 ATTORNEY DOCKET NO.: ASC-063 INFORMATION DISCLOSURE STATEMENT APPLICANT(S): Currie et al. SERIAL NO.: 10/696,994 FILING DATE: October 30, 2003 GROUP: 2811 **U.S. PATENT DOCUMENTS** EXAM. DOCUMENT DATE NAME **CLASS** SUB FILING DATE IF INIT. NUMBER **CLASS** APPROPRIATE 08/15/1995 Αl 5,442,205 Brasen et al. 08/09/1993 5.726.087 03/10/1998 A2 Tseng et al. 06/09/1994 A3 5,780,922 07/14/1998 Mishra et al. 11/27/1996 A4 6,107,653 08/22/2000 Fitzgerald 06/23/1998 09/04/2001 Α5 6,284,615 B1 Pinto et al. 06/16/1999 US2002/0068393 A1 06/06/2002 **A6** Fitzgerald et al. 08/06/2001 A7 US2003/02302333 A1 12/18/2003 Fitzgerald et al. 03/19/2003 US2004/0031979 A1 02/19/2004 Lochtefeld et al. 06/06/2003 A8 FOREIGN PATENT DOCUMENTS DOCUMENT SUB EXAM. DATE COUNTRY CLASS FILING ABSTRACT ENGLISH INIT. NUMBER CODE CLASS DATE ONLY LANG (Y/N) BI 01/022482 A1 03/29/2001 wo N Y 01/03/2003 B2 03/001607 A1 WO Ν Y OTHER ART, JOURNAL ARTICLES, ETC. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) EXAM. INIT. Currie et al., "Carrier Mobilities and Process Stability of Strained Si n- and p-MOSFETs on SiGe virtual C1 substrates," J. Vac. Sci. Technol. B, 19(6):2268-2279 (2001). Kummer et al., "Low Energy Plasma Enhanced Chemical Vapor Deposition," Mat. Sci. & Eng. B89, 288-C2. 295 (2002). Leitz et al., "Hole mobility enhancements and alloy scattering-limited mobility in tensile strained Si/SiGe C3 surface channel metal-oxide-semiconductor field-effect transistors," Journal of Applied Physics, 92(7):3745-3751 (2002). Lucovsky et al., "Low-temperature plasma-assisted oxidation of Si: a new approach for creation of device-C4 quality Si-SiO₂ interfaces with deposited dielectrics for applications in Si MOSFET technologies," Journal of Non-Crystalline Solids, 179 354-366 (1994). C5 Pal et al., "Gd₂O₃, Ga₂O₃ (Gd₂O₃), Y₂O₃, and Ga₂O₃, as high-k gate dielectrics on SiGe: A comparative study," Journal of Applied Physics, 90(8):4103-4107 (2001). Sugii et al., "Role of Si_{1.x}Ge, buffer layer on mobility enhancement in a strained-Si n-channel metal-oxide-C6 semiconductor field-effect transistor," Applied Physics Letters, 75(19):2948-2950 (1999). Invitation to Pay Additional Fees for International Application No. PCT/US 03/34576 mailed on December C7 17, 2004, 7 pages. DATE CONSIDERED **EXAMINER**